To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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4AM13

Silicon N-Channel/P-Channel Power MOS FET Array

ADE-208-1211 (Z)
1st. Edition
Mar. 2001

Application

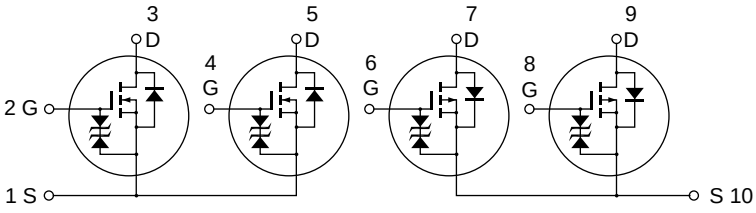
High speed power switching

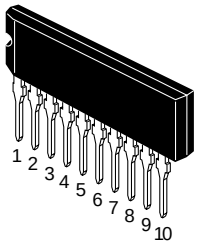
Features

- Low on-resistance
  N-channel: $R_{DS(on)} \leq 0.4$, V_{GS} = 10 V, I_D = 1.5 A
  P-channel: $R_{DS(on)} \leq 0.45$, V_{GS} = –10 V, I_D = –1.5 A
- Capable of 4 V gate drive
- Low drive current
- High speed switching
- High density mounting
- Suitable for H-bridged motor driver

Outline

SP-10





1, 10. Source
2, 4, 6, 8. Gate
3, 5, 7, 9. Drain

Absolute Maximum Ratings (Ta = 25°C) (1 Unit)

Item	Symbol	Rating		Unit
		Nch	Pch	
Drain to source voltage	V_{DSS}	60	–60	V
Gate to source voltage	V_{GSS}	±20	±20	V
Drain current	I_D	3	–3	A
Drain peak current	$I_{D(pulse)}$*[1]	12	–12	A
Body to drain diode reverse drain current	I_{DR}	3	–3	A
Channel dissipation	Pch (Tc = 25°C)*[2]	28		W
Channel dissipation	Pch*[2]	4		W
Channel temperature	Tch	150		°C
Storage temperature	Tstg	–55 to +150		°C

Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. 4 Devices operation

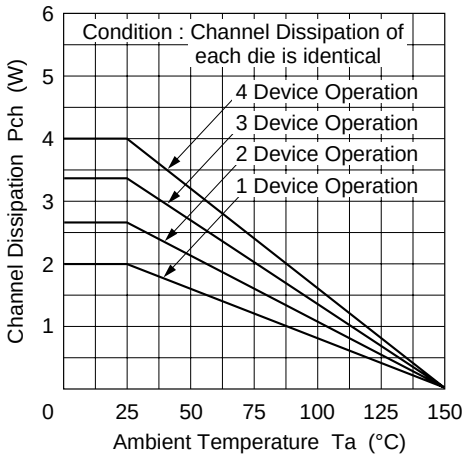
Electrical Characteristics (Ta = 25°C) (1 Unit)

		N channel			P channel				
Item	**Symbol**	**Min**	**Typ**	**Max**	**Min**	**Typ**	**Max**	**Unit**	**Test conditions**
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	–60	—	—	V	I_D = 10 mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	±20	—	—	V	I_G = ±100 µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	—	—	±10	µA	V_{GS} = ±16 V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	250	—	—	–250	µA	V_{DS} = 50 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	–1.0	—	–2.0	V	I_D = 1 mA, V_{DS} = 10 V
Static drain to source on state resistance	$R_{DS(on)}$	—	0.25	0.35	—	0.28	0.4	Ω	I_D = 1.5 A, V_{GS} = 10 V*[1]
		—	0.35	0.5	—	0.4	0.55	Ω	I_D = 1.5 A, V_{GS} = 4 V*[1]
Forward transfer admittance	$\|y_{fs}\|$	1.5	2.5	—	1.5	2.5	—	S	I_D = 1.5 A, V_{DS} = 10 V*[1]
Input capacitance	Ciss	—	240	—	—	400	—	pF	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz
Output capacitance	Coss	—	115	—	—	240	—	pF	
Reverse transfer capacitance	Crss	—	35	—	—	70	—	pF	
Turn-on delay time	$t_{d(on)}$	—	4	—	—	5	—	ns	I_D = 1.5 A, V_{GS} = 10 V, R_L = 20 Ω
Rise time	t_r	—	20	—	—	25	—	ns	
Turn-off delay time	$t_{d(off)}$	—	80	—	—	180	—	ns	
Fall time	t_f	—	40	—	—	80	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.2	—	—	–1.1	—	V	I_F = 3 A, V_{GS} = 0
Body to drain diode reverse recovery time	t_{rr}	—	75	—	—	140	—	ns	I_F = 3 A, V_{GS} = 0, dIF/dt = 50 A/µs

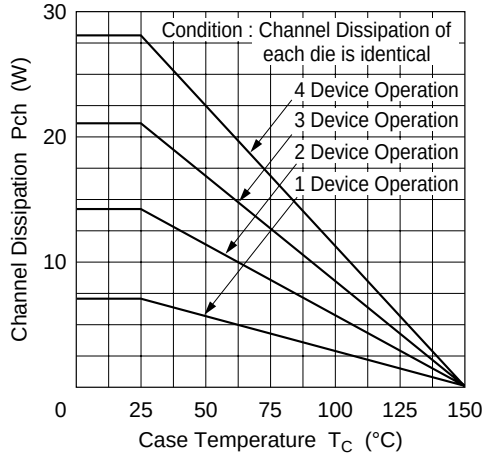
Note: 1. Pulse Test

Polarity of test conditions for P channel device is reversed.

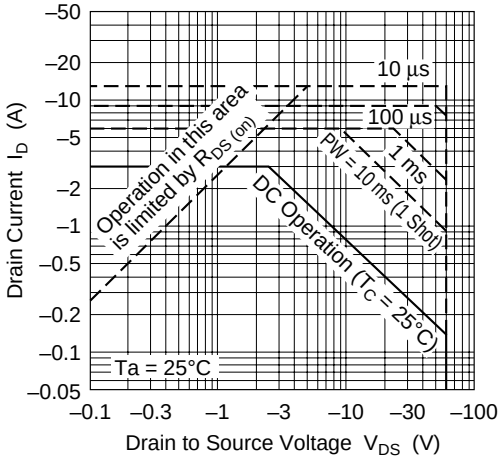
Maximum Channel Dissipation Curve



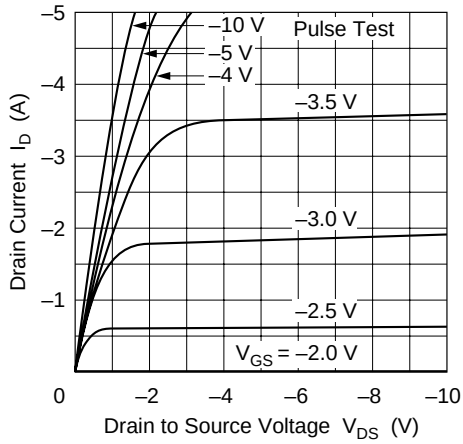
Maximum Channel Dissipation Curve



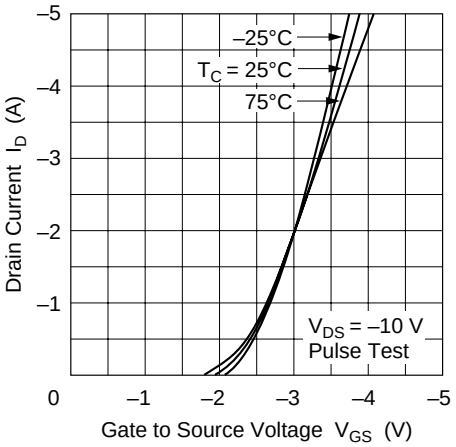
Maximum Safe Operation Area
(P-Channel)



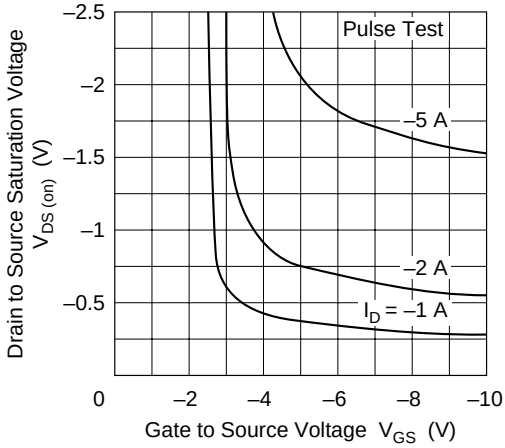
Typical Output Characteristics



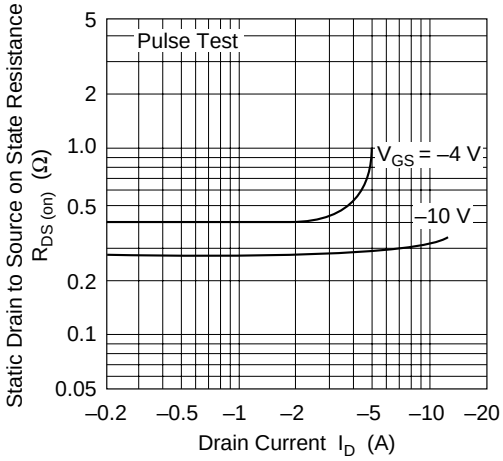
Typical Transfer Characteristics



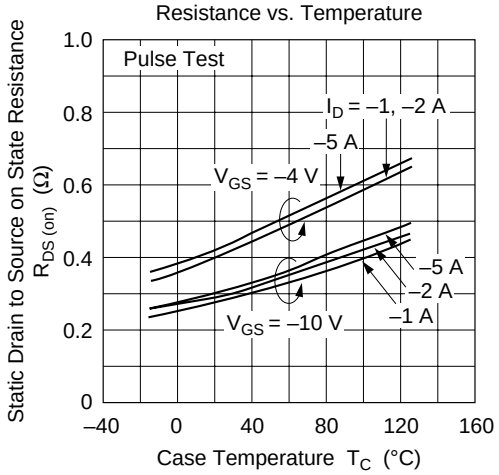
Drain to Source Saturation Voltage vs. Gate to Source Voltage



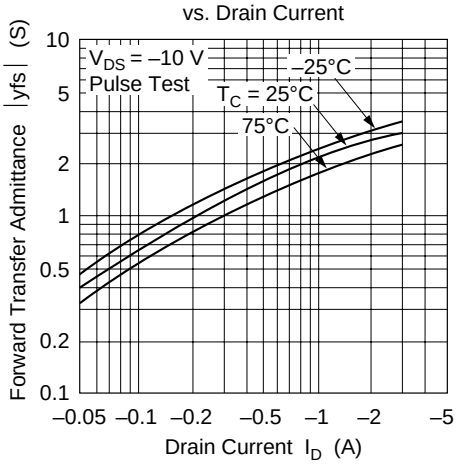
Static Drain to Source on State Resistance vs. Drain Current



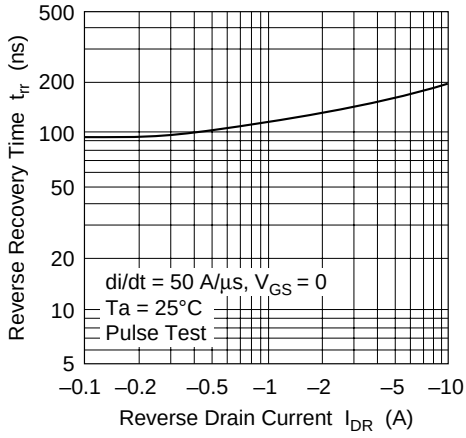
Static Drain to Source on State Resistance vs. Temperature



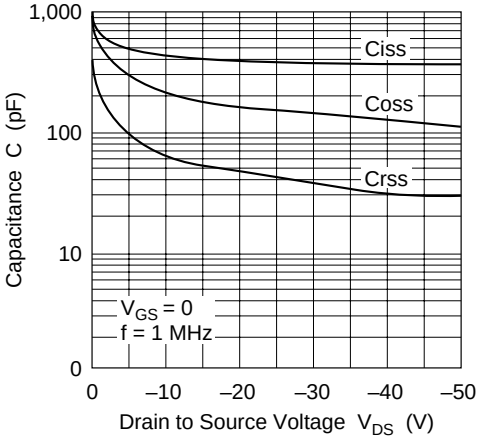
Forward Transfer Admittance vs. Drain Current



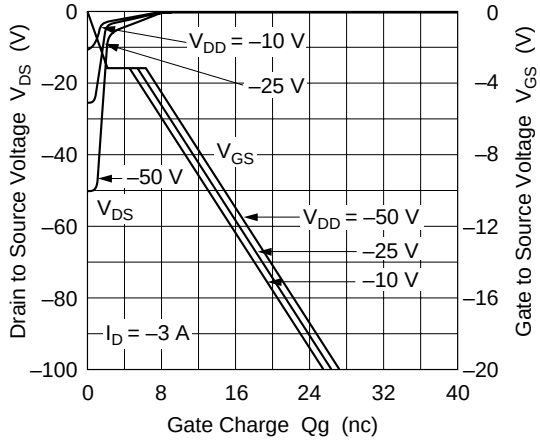
Body to Drain Diode Reverse Recovery Time



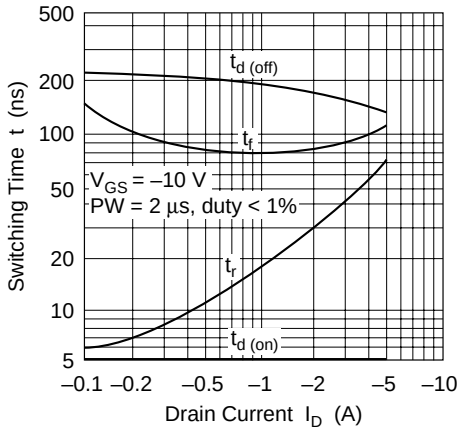
Typical Capacitance vs. Drain to Source Voltage



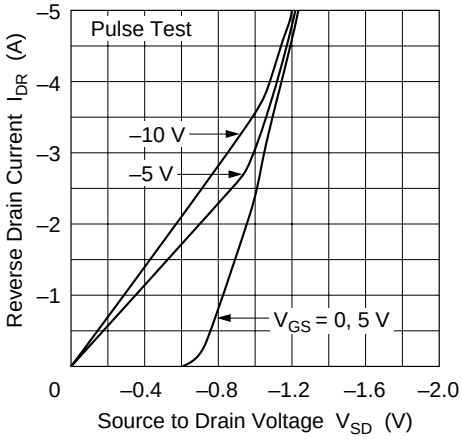
Dynamic Input Characteristics



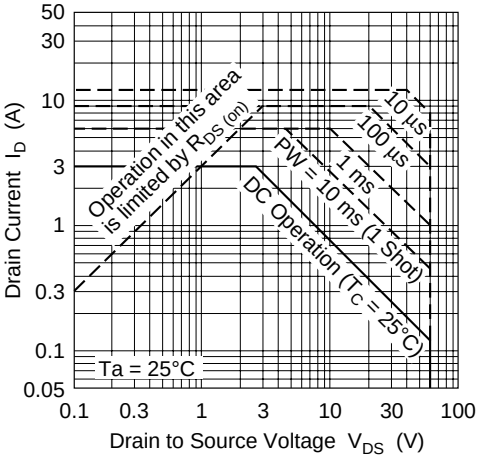
Switching Characteristics



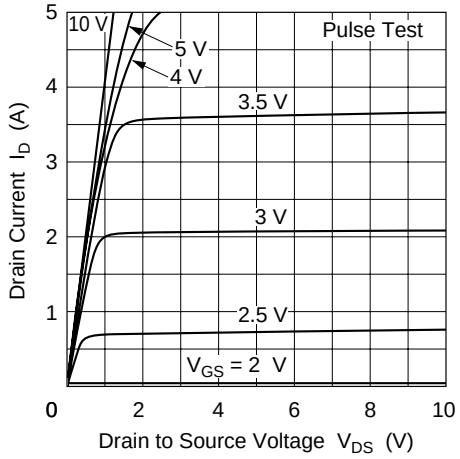
Reverse Drain Current vs.
Source to Drain Voltage



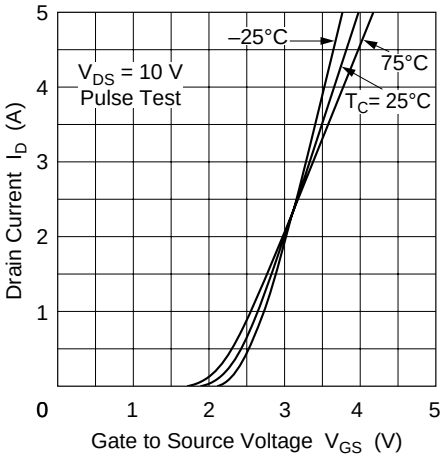
Maximum Safe Operation Area
(N-Channel)



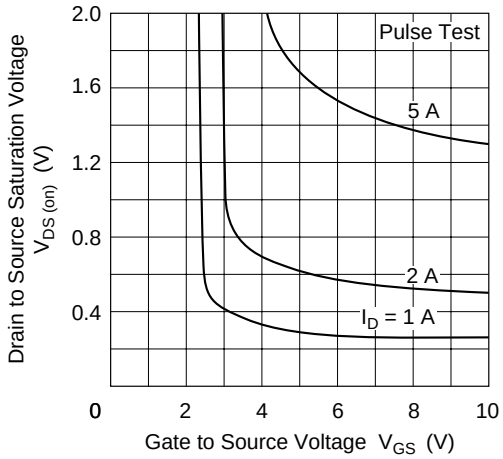
Typical Output Characteristics



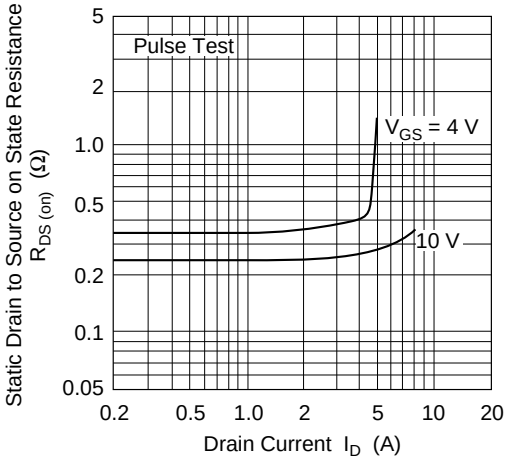
Typical Transfer Characteristics



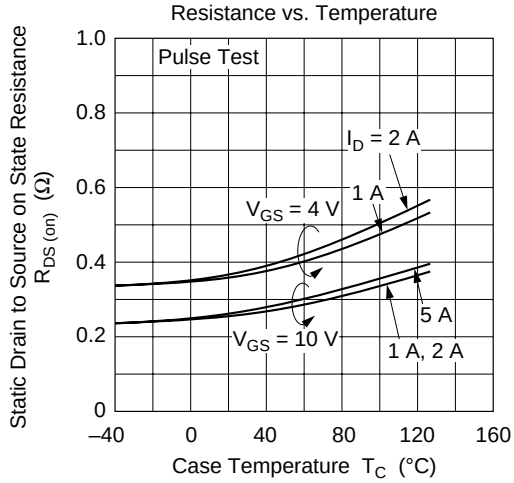
Drain to Source Saturation Voltage
vs. Gate to Source Voltage



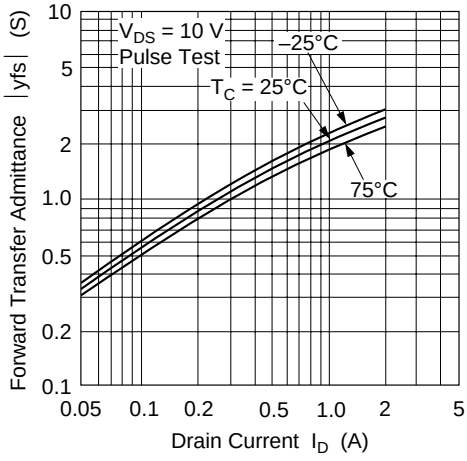
Static Drain to Source on State Resistance vs. Drain Current



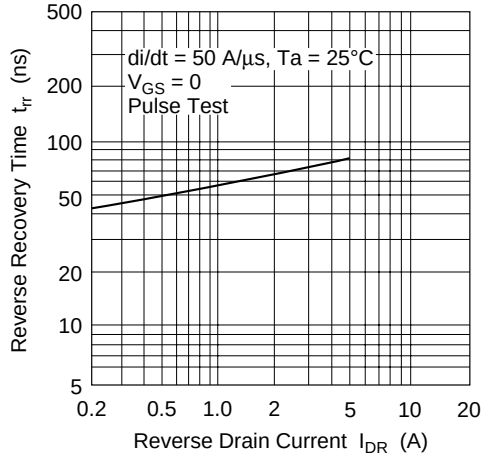
Static Drain to Source on State Resistance vs. Temperature



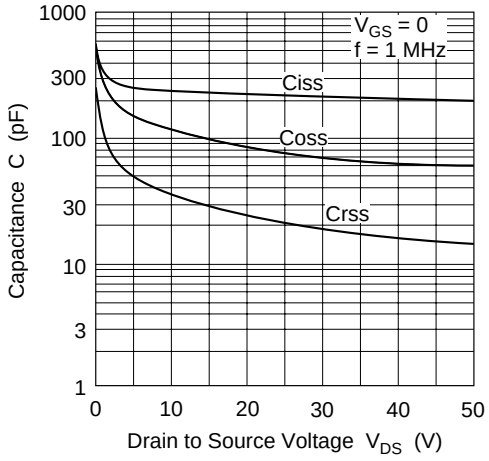
Forward Transfer Admittance vs. Drain Current



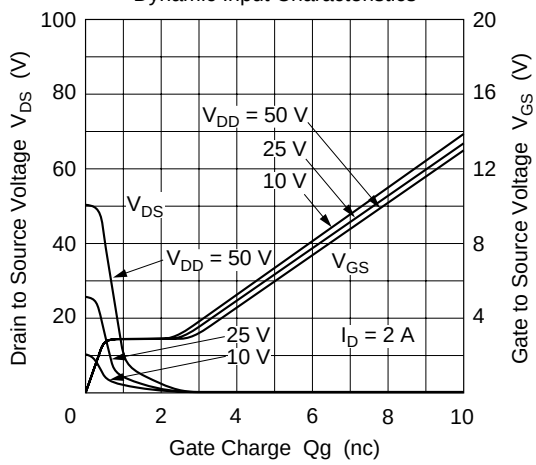
Body to Drain Diode Reverse Recovery Time



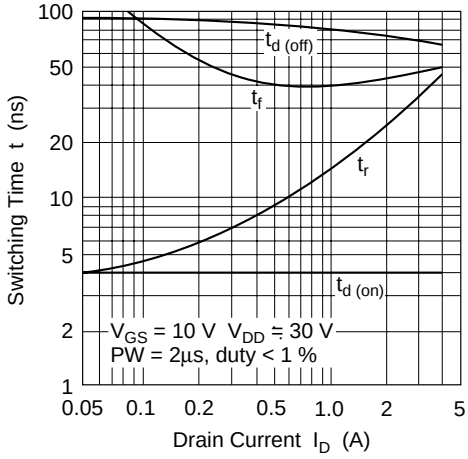
Typical Capacitance vs.
Drain to Source Voltage



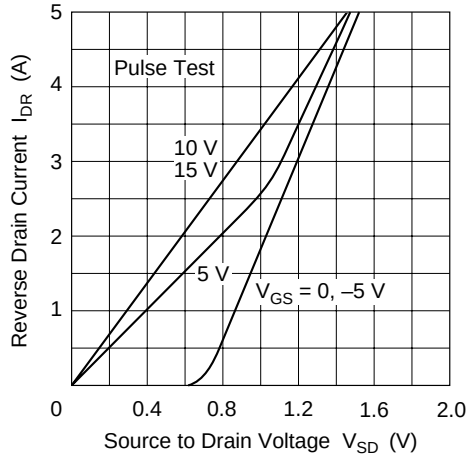
Dynamic Input Characteristics



Switching Characteristics



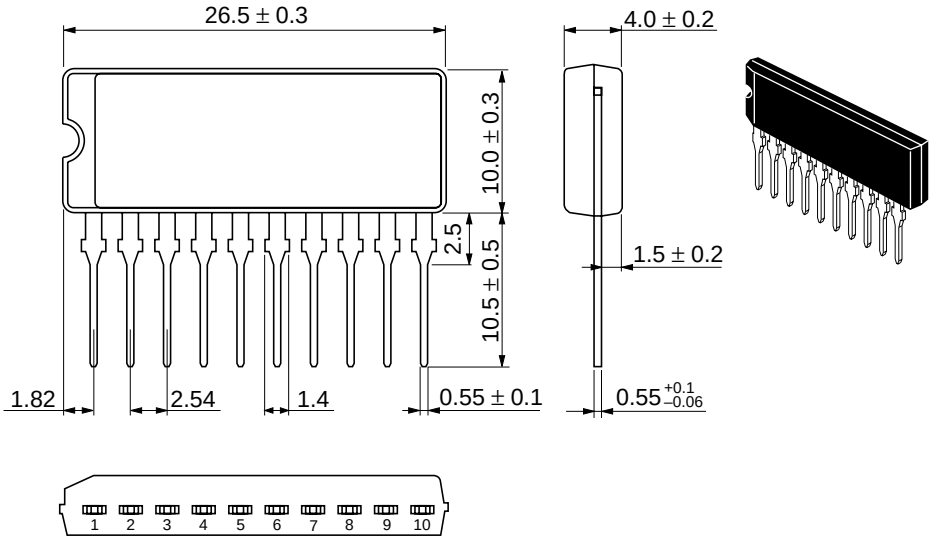
Reverse Drain Current vs.
Source to Drain Voltage



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	SP-10
JEDEC	—
EIAJ	—
Mass (reference value)	2.9 g

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Colophon 2.0

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